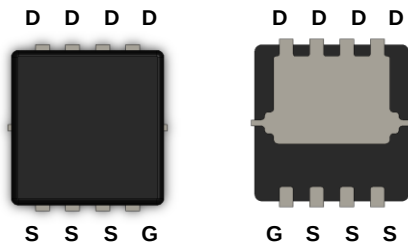


General Description

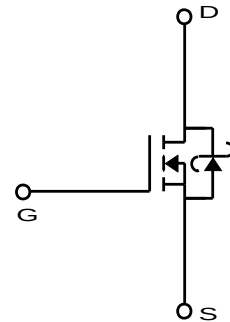
The MDV1595S uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDV1595S is suitable for DC/DC converter and general purpose applications.

Features

- $V_{DS} = 30V$
- $I_D = 36.1A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 10.7m\Omega$ @ $V_{GS} = 10V$
 $< 13.0m\Omega$ @ $V_{GS} = 4.5V$
- 100% UIL Tested
- 100% Rg Tested
- SBD Built In



PDFN33



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	30	V
Gate-Source Voltage		V_{GSS}	± 12	V
Continuous Drain Current ⁽¹⁾	$T_C = 25^\circ C$	I_D	36.1	A
	$T_C = 100^\circ C$		22.8	
	$T_A = 25^\circ C$		13.4 ⁽³⁾	
	$T_A = 70^\circ C$		10.8 ⁽³⁾	
Pulsed Drain Current		I_{DM}	80	A
Power Dissipation	$T_C = 25^\circ C$	P_D	24.5	W
	$T_C = 100^\circ C$		9.8	
	$T_A = 25^\circ C$		3.4 ⁽³⁾	
	$T_A = 70^\circ C$		2.2 ⁽³⁾	
Single Pulse Avalanche Energy ⁽²⁾		E_{AS}	48	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	36	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	5.1	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDV1595SURH	-55~150°C	PDFN33	Tape & Reel	Halogen Free

Electrical Characteristics (T_J = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	30	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	1.5	2.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 30V, V _{GS} = 0V T _J =125°C	-	-	0.5 100	mA
Gate Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0V	-	-	±100	nA
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 13A T _J =125°C	-	8.2	10.7	mΩ
		V _{GS} = 4.5V, I _D = 11A	-	10.0	13.0	
			-	14.9	13.5	
Forward Transconductance	g _{fs}	V _{DS} = 5V, I _D = 13A	-	27.3	-	S
Dynamic Characteristics						
Total Gate Charge	Q _{g(10V)}	V _{DS} = 15.0V, I _D = 13A, V _{GS} = 10V	15.6	22.3	29.0	nC
Total Gate Charge	Q _{g(4.5V)}		6.9	9.9	12.9	
Gate-Source Charge	Q _{gs}		-	3.0	-	
Gate-Drain Charge	Q _{gd}		-	2.7	-	
Input Capacitance	C _{iss}	V _{DS} = 15.0V, V _{GS} = 0V, f = 1.0MHz	-	1426	1853	pF
Reverse Transfer Capacitance	C _{rss}		-	75.4	98	
Output Capacitance	C _{oss}		-	198	257	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 15.0V, I _D = 13A, R _G = 3.0Ω	-	7.8	-	ns
Rise Time	t _r		-	3.1	-	
Turn-Off Delay Time	t _{d(off)}		-	33.5	-	
Fall Time	t _f		-	4.3	-	
Gate Resistance	R _g	f=1 MHz	0.5	1.0	2.0	Ω
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V	-	0.45	0.7	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 13A, dI/dt = 100A/μs	-	24.2	36.3	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	16.4	24.6	nC

Note :

1. Surface mounted FR4 board with 2oz. Copper. Continuous current at T_C=25°C is silicon limited.
2. E_{AS} is tested at starting T_J = 25°C, L = 0.1mH, I_{AS} = 16.8A, V_{DD} = 27V, V_{GS} = 10V.
3. T < 10sec

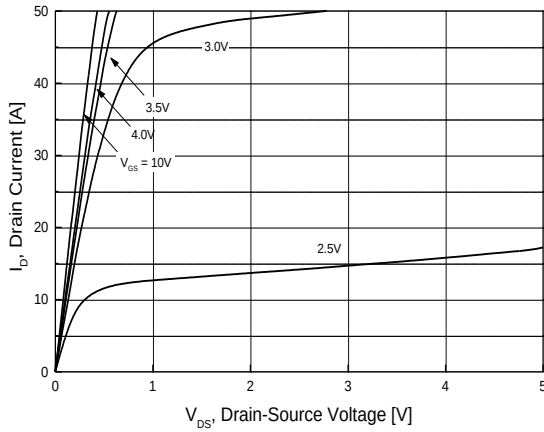


Fig.1 On-Region Characteristics

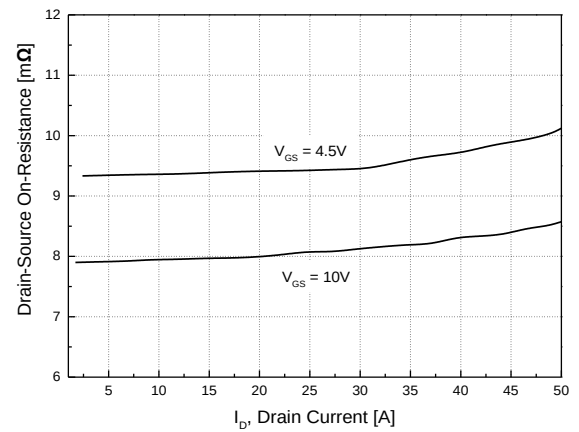


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

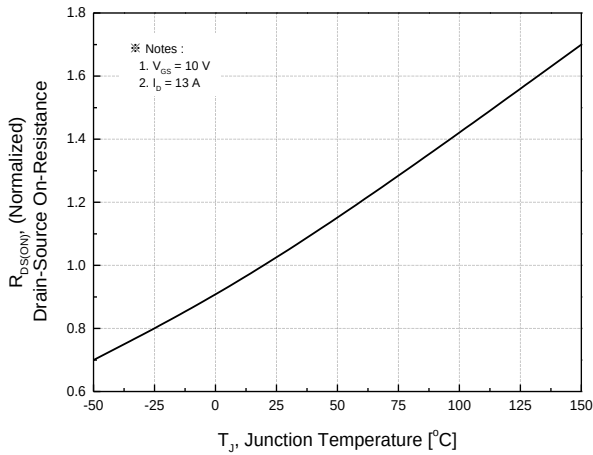


Fig.3 On-Resistance Variation with

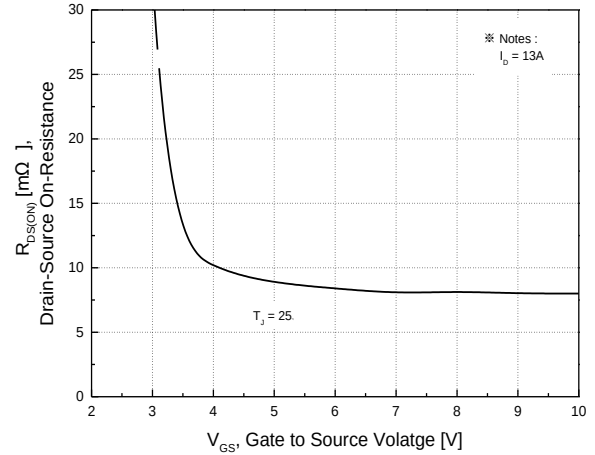


Fig.4 On-Resistance Variation with Gate to Source Voltage

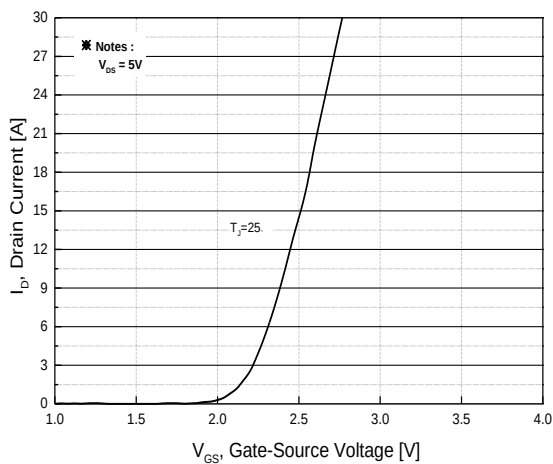


Fig.5 Transfer Characteristics

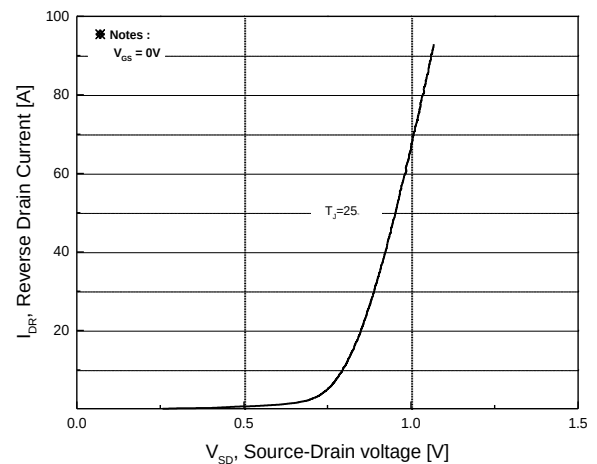
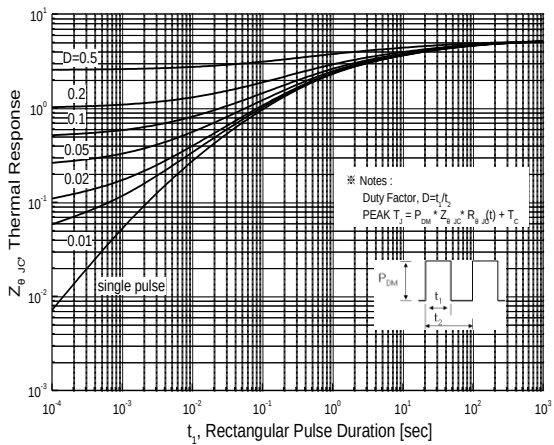
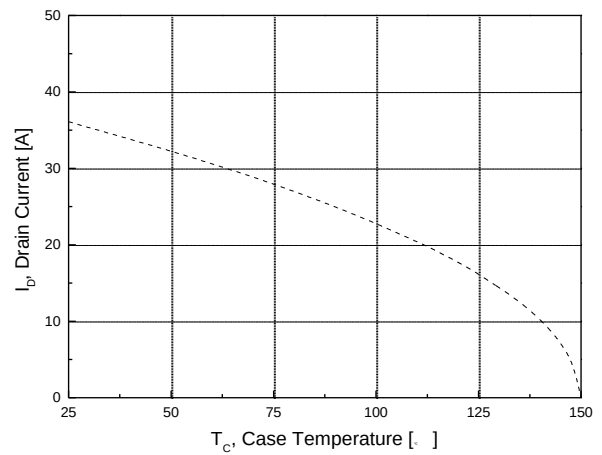
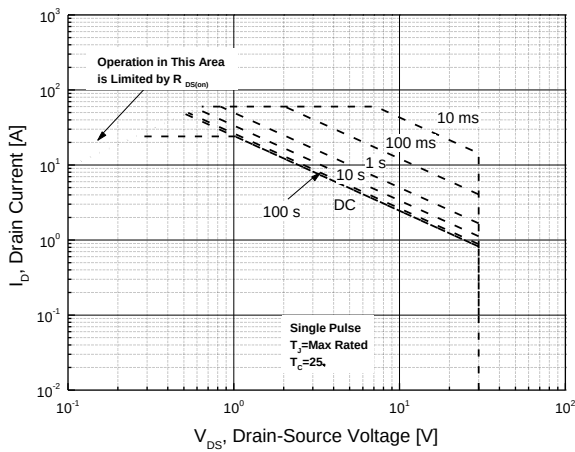
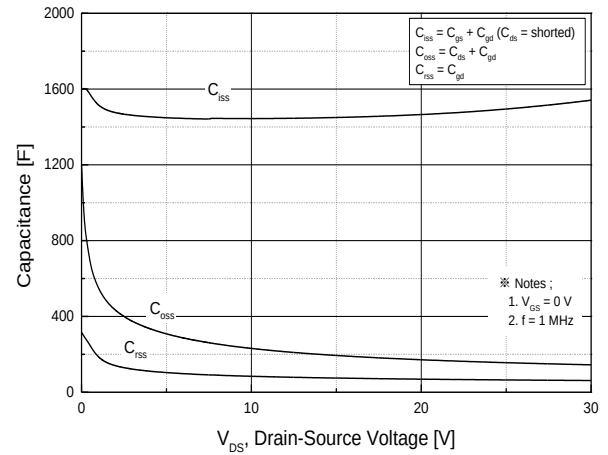
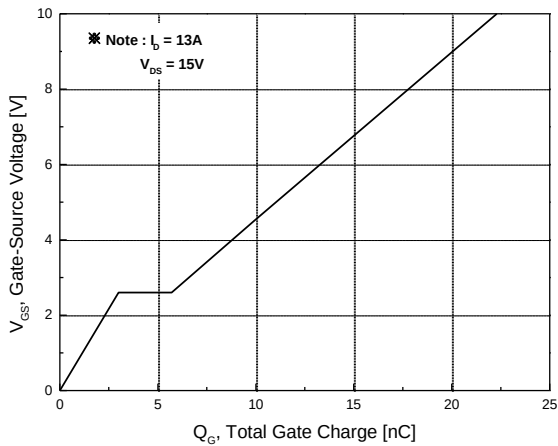


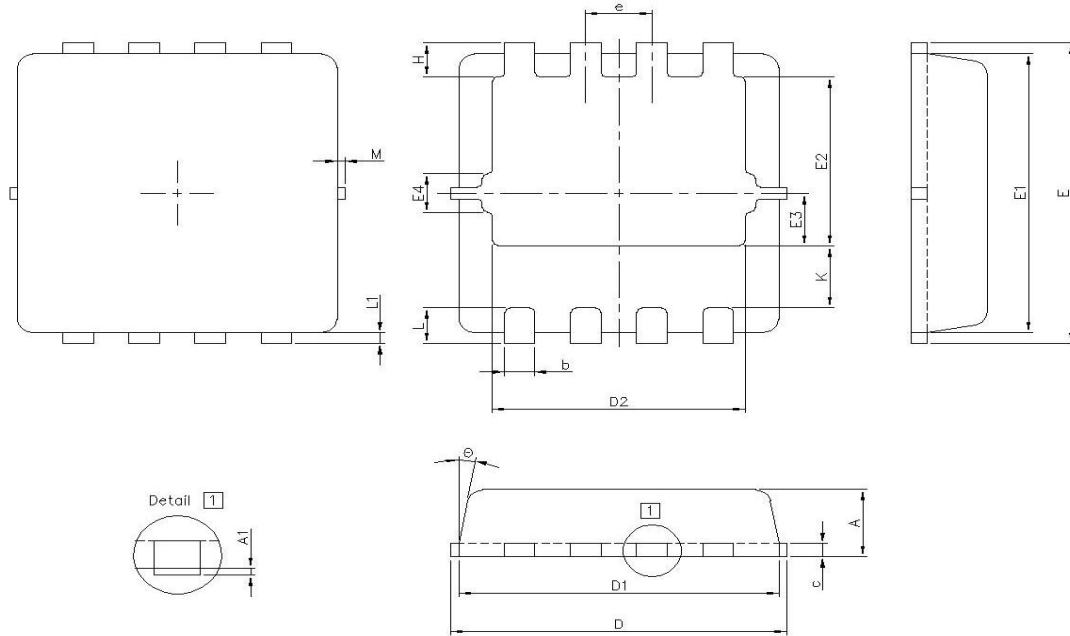
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Package Dimension

PDFN33 (3.3x3.3mm)

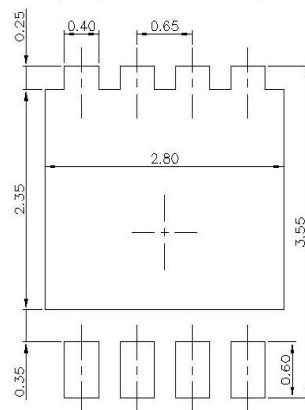
Dimensions are in millimeters, unless otherwise specified



(Unit: mm)

DIM	Min	Max	DIM	Min	Max
A	0.70	0.80	E2	1.78	1.98
A1	0.00	0.05	E3	0.49	0.69
b	0.25	0.35	E4	0.35 TYP.	
c	0.10	0.25	e	0.65 BSC	
D	3.20	3.40	K	0.70 TYP.	
D1	3.00	3.20	L	0.30	0.50
D2	2.39	2.59	L1	0.13 TYP.	
E	3.25	3.45	H	0.27	0.47
E1	3.00	3.20	Θ	0	12

Land Pattern
(Only for Reference)



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